



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

TO-220AK Plastic-Encapsulate Thyristors

BTA06 3Q TRIACs

MAIN CHARACTERISTICS

$I_{T(RMS)}$		6A
V_{DRM}/V_{RRM}	BTA06-600(T/S/C)W	600V
	BTA06-800(T/S/C)W	800V
V_{TM}		1.55V

FEATURES

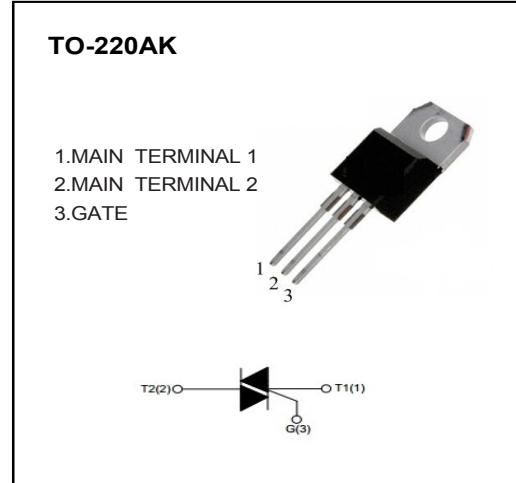
- NPNPN 5-layer Structure TRIACs
- Mesa Glass Passivated Technology
- Multi Layers Metal Electrodes
- High Junction Temperature
- Good Commutation Performance
- High dV/dt and di/dt
- Insulating Voltage=2500V_(RMS)

APPLICATIONS

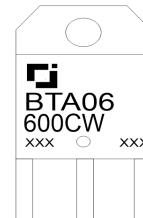
- Heater Control
- Motor Speed Controller
- Mixer

ABSOLUTE RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test condition		Value		Unit
V_{DRM}/ V_{RRM}	Repetitive peak off-state voltage	$T_j=25^\circ\text{C}$	BTA06-600(T/S/C)W	600		V
			BTA06-800(T/S/C)W	800		V
$I_{T(RMS)}$	RMS on-state current	TO-220AK($T_c \leq 105^\circ\text{C}$), Fig. 1,2		6		A
I_{TSM}	Non repetitive surge peak on-state current	Full sine wave , $T_j(\text{init})=25^\circ\text{C}$, $tp=20\text{ms}$; Fig. 3,5		60		A
I^2t	I^2t value	$tp=10\text{ms}$		21		A^2s
di_T/dt	Critical rate of rise of on-state current	$I_G=2*I_{GT}$, $tr \leq 10\text{ns}$, $F=120\text{Hz}$, $T_j=125^\circ\text{C}$	$I - II - III$	50		$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$tp=20\mu\text{s}$, $T_j=125^\circ\text{C}$		4		A
$P_{G(AV)}$	Average gate power	$T_j=125^\circ\text{C}$		1		W
T_{STG}	Storage temperature			-40~+150		$^\circ\text{C}$
T_j	Operating junction temperature			-40~+125		



MARKING



BTA06:Series Code

600CW:Depends on V_{DRM} and I_{GT}

XXX:Internal Code

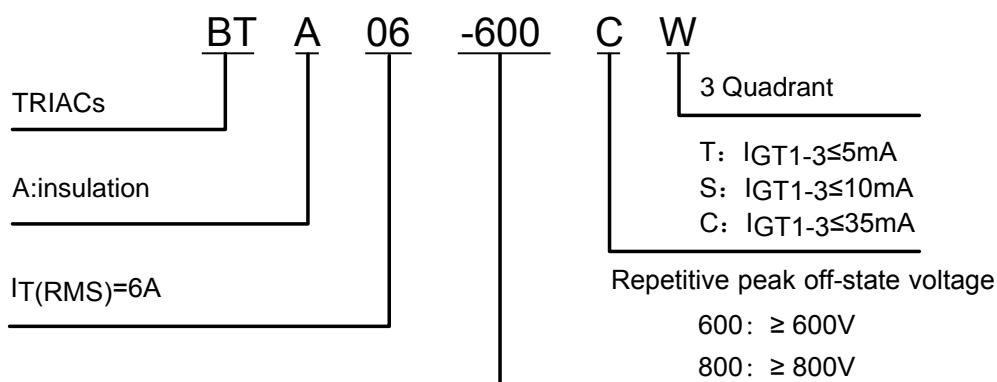
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Value			Unit	
			TW	SW	CW		
I_{GT}	Gate trigger current	$V_D=12\text{V}$, $R_L=30\Omega$, $T_j=25^\circ\text{C}$, Fig. 6	I - II - III	≤ 5	≤ 10	≤ 35	mA
V_{GT}	Gate trigger voltage		I - II - III	≤ 1.3			V
V_{GD}	Non-triggering gate voltage	$V_D=V_{DRM}$, $T_j=125^\circ\text{C}$		≥ 0.2			V
I_H	Holding current	$I_T=100\text{mA}$, Fig. 6		≤ 10	≤ 15	≤ 35	mA
I_L	Latching current	$I_G=1.2I_{GT}$, Fig. 6	I - III	≤ 10	≤ 25	≤ 50	mA
			II	≤ 15	≤ 30	≤ 60	mA
dV_D/dt	Critical rate of rise of off-state	$V_D=67\%V_{DRM}$, Gate Open $T_j=125^\circ\text{C}$		≥ 20	≥ 40	≥ 400	V/ μs
V_{TM}	On-state Voltage	$I_{TM}=8.5\text{A}$, $t_p=380\mu\text{s}$, Fig. 4		≤ 1.55			V
I_{DRM} / I_{RRM}	Repetitive peak off-state current	$V_D=V_{DRM}/V_{RRM}$, $T_j=25^\circ\text{C}$		≤ 5	≤ 5	≤ 5	μA
		$V_D=V_{DRM}/V_{RRM}$, $T_j=125^\circ\text{C}$		≤ 1.0	≤ 1.0	≤ 1.0	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th} (j-c)$	Junction to case (AC)	2.7	$^\circ\text{C/W}$
$R_{th} (j-a)$	Junction to ambient	60	$^\circ\text{C/W}$

PART NUMBER



CHARACTERISTICS CURVES

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

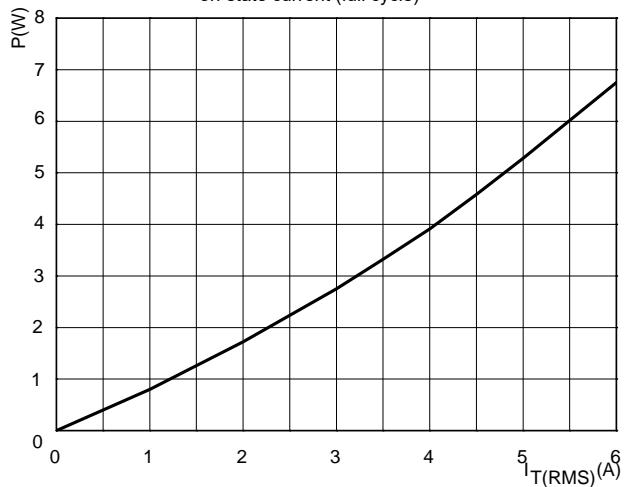


FIG.2: RMS on-state current versus case temperature (full cycle)

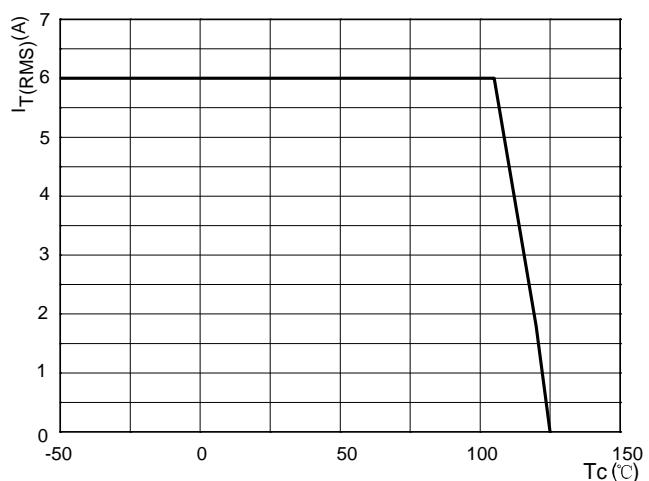


FIG.3: Surge peak on-state current versus number of cycles

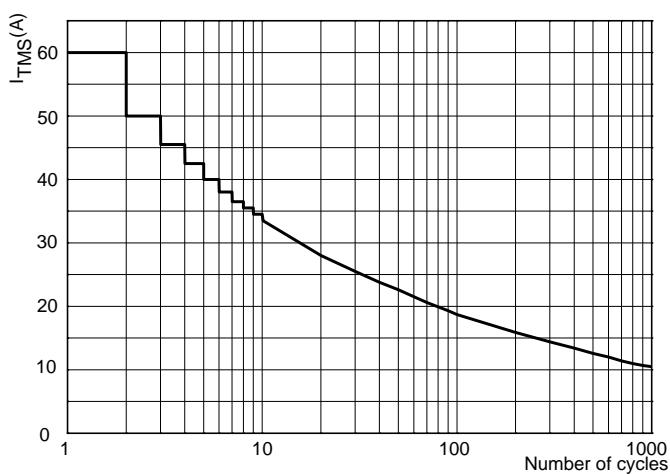


FIG.4: On-state characteristics (maximum values)

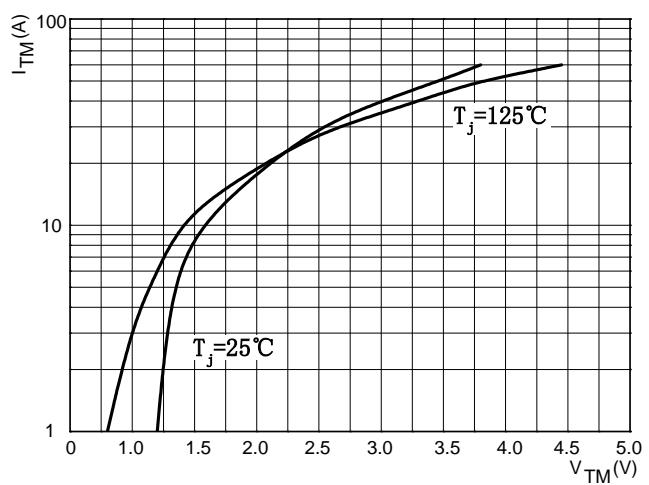


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

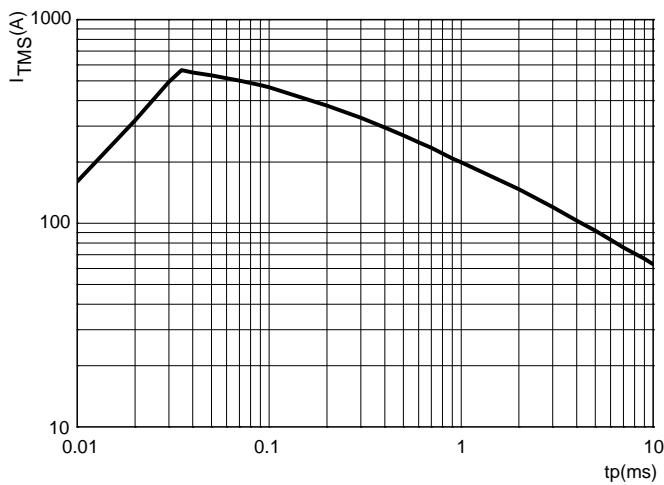
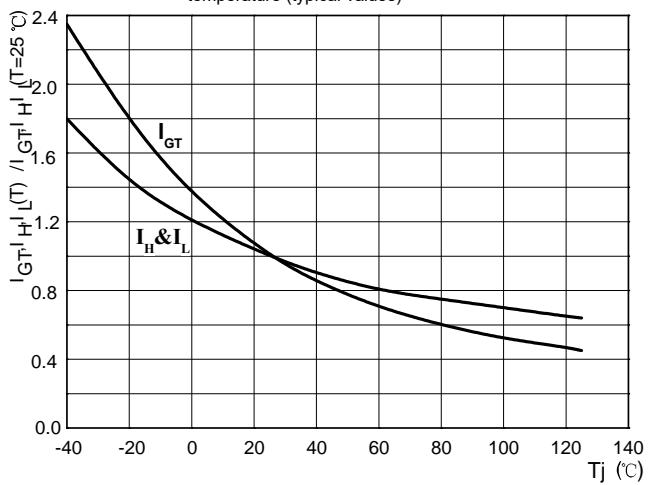
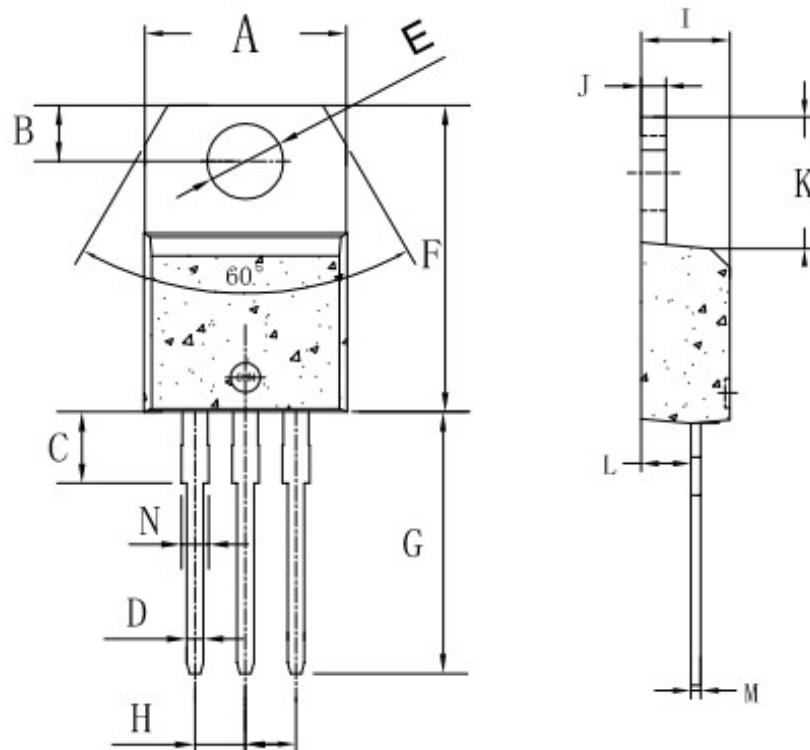


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



TO-220AK PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.8	10.4	0.385	0.409
B	2.65	3.1	0.104	0.122
C	2.8	4.2	0.110	0.165
D	0.7	0.92	0.027	0.036
E	3.75	3.95	0.147	0.155
F	14.8	16.1	0.582	0.633
G	13.05	13.6	0.513	0.535
H	2.4	2.7	0.094	0.106
I	4.38	4.61	0.172	0.181
J	1.15	1.36	0.045	0.053
K	5.85	6.82	0.230	0.268
L	2.35	2.75	0.092	0.108
M	0.35	0.65	0.013	0.025
N	1.18	1.42	0.046	0.055